

# **KH232**

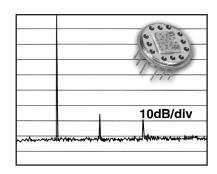
## **Low Distortion Wideband Op Amp**

#### **Features**

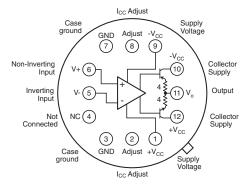
- -69dBc 2nd and 3rd harmonics at 20MHz
- -3dB bandwidth of 270MHz
- 0.05% settling in 15ns
- 3000V/µs slew rate
- 1mV input offset voltage, 10µV/°C drift
- ±10V, 100mA max output
- Direct replacement for CLC232

## **Applications**

- Flash A/D drivers
- DAC current-to-voltage conversion
- Wide dynamic range IF amps
- VCO drivers
- DDS postamps
- Radar/communication receivers
- Precision line drivers



#### **Bottom View**



Pins 2 and 8 are used to adjust the supply current or to adjust the offset voltage (see text). These pins are normally left unconnected.

## **General Description**

The KH232 is a wideband low distortion operational amplifier designed specifically for high speed, low gain applications requiring wide dynamic range. Utilizing a current feedback architecture, the KH232 offers high speed performance while maintaining DC precision.

The KH232 offers precise gains from  $\pm 1$  to  $\pm 5$  with a true 0.1% linearity and provides stable, oscillation-free operation across the entire gain range without external compensation. The KH232, a pin compatible enhanced version of the KH231, reduces 2nd and 3rd harmonic distortion to an extremely low -69dBc at 20MHz (2V<sub>pp</sub>, R<sub>L</sub> = 100 $\Omega$ ). Additional features provided by the KH232 include a small signal bandwidth of 270MHz, a large signal bandwidth of 95MHz and a 3000V/ $\mu$ s slew rate. The input offset voltage is typically 1mV with an input offset drift of  $10\mu$ V/°C.

The KH232 combines these high performance features with its 0.05% settling time of 15ns and its 100mA drive capability to provide high speed, high resolution A/D and D/A converter systems with an attractive solution for driving and buffering. Wide dynamic range systems such as radar and communication receivers requiring low harmonic distortion and low noise will find the KH232 to be an excellent choice. As a line driver, the KH232 set at a gain of 2 cancels matched line losses.

The KH232 is constructed using thin film resistor/bipolar transistor technology, and is available in the following versions:

KH232AI	-25°C to +85°C	12-pin TO-8 can
KH232AK	-55°C to +125°C	12-pin TO-8 can, features burn-in & hermetic testing
KH232AM	-55°C to +125°C	12-pin TO-8 can, environmentally screened and electrically
		tested to MIL-STD-883
KH232HXC	-55°C to +125°C	SMD#: 5962-9166501HXC
KH232HXA	-55°C to +125°C	SMD#: 5962-9166501HXA

### **Typical Performance**

	Gain Setting						
Parameter	1	2	5	-1	-2	-5	Units
-3dB bandwidth	430	270	135	220	175	110	MHz
rise time (2V)	1.8	2.0	2.5	2.0	2.2	2.9	ns
slew rate	2.5	3.0	3.0	3.0	3.0	3.0	V/ns
settling time (to 0.1%)	12	12	12	12	12	15	ns

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KH232 Electrical Characteristics ( $T_A = +25$ °C,  $A_V = +2V$ ,  $V_{CC} = \pm 15V$ ,  $R_L = 100\Omega$ ,  $R_f = 250\Omega$ ; unless specified)

Ambient Temperature   KH232A   425°C   -25°C   +25°C   +25°C     -425°C     -425°C	PARAMETERS	CONDITIONS	TYP MIN & MAX RATINGS		INGS	UNITS	SYM	
FREQUENCY DOMAIN RESPONSE   -3dB bandwidth (note 2)	Ambient Temperature	KH232AI	+25°C	-25°C	+25°C	+85°C		
+ 3dB bandwidth (note 2)	Ambient Temperature	KH232AK/AM/HXC/HXA	+25°C	-55°C	+25°C	+125°C		
large-signal bandwidth   V, \$100/pp   95   >80   >80   >60   MHz   FPBW   FP	FREQUENCY DOMAIN RESPONSE							
large-signal bandwidth gain flatness (note 2)   V <sub>0</sub> ≤0.68V <sub>pp</sub>   1	+ -3dB bandwidth (note 2)	$V_0 \leq 0.63V_{pp}$					II .	
gain flatness (note 2)	large-signal bandwidth	V <sub>o</sub> ≥∠V <sub>pp</sub> V <sub>o</sub> <10V <sub>pp</sub>		ll .				
peaking		V <sub>0</sub> ≤0.63V <sub>pp</sub>			, 00			
ricolloff	t peaking	0.1 to 50MHz					II .	
group delay   to 100MHz   3.5 ± 0.5   -   -   -   -     -     S   GD   Inear phase deviation   to 100MHz   0.5   <2.0   <2.0   <2.0   °   C.PD   C	1 3			ll .			II .	
Innear phase deviation reverse isolation non-inverting inverting isolation non-inverting inverting   53   543   543   543   548				<0.6	<0.6	<1.0		
Triverse isolation   S3   S43   S				-2 O	-20	-20		
Noise and participation   Sample   S		to Toolvii iz	0.5	\2.0	\2.0	\2.0		
Inverting   Section   S			53	>43	>43	>43	dB	RINI
rise and fall time	· · · · · · · · · · · · · · · · · · ·			>26	>26	>26	dB	RIIN
Settling time to 0.05%   5V step   15	TIME DOMAIN RESPONSE							
Settling time to 0.05%   5V step   15   -   -   -   ns   TS	rise and fall time	2V step	2.0	<2.4	<2.3	<2.7	ns	TRS
To 0.1%   2.5V step   12				<7.0	<6.5	<6.5	ns	
SV step   SV				ll .			II .	
Slew rate (overdriven input) overload recovery		•	II I				II .	
NOISE AND DISTORTION RESPONSE   120		5v step					II .	
NOISE AND DISTORTION RESPONSE		<1% error	3.0	>2.5	>2.5	>1.0	V/115	on .
+ 2nd harmonic distortion         2V <sub>pp</sub> , 20MHz         -69         <-64		V170 01101	120	_	_	_	ns	OR
+ 2nd harmonic distortion         2V <sub>pp</sub> , 20MHz         -69         <-64	NOISE AND DISTORTION RESPONSE							
+ 3rd harmonic distortion equivalent input noise         2V <sub>pp</sub> , 20MHz         -69         <-64	+ 2nd harmonic distortion	2V <sub>pp</sub> , 20MHz	-69	<-64	<-64	<-56	dBc	HD2
Part	+ 3rd harmonic distortion	2V <sub>pp</sub> , 20MHz	-69	<-64	<-64	<-64	dBc	HD3
Inverting current   >100kHz   20   <23   <23   <25   pAV/Hz   ICN   non-inverting current   >100kHz   2.3   <2.6   <2.6   <2.9   pAV/Hz   NCN								
Non-inverting current noise floor   Signature   Sig								
Noise floor								
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				ll .				
Integrated noise   SMHz to 200MHz   S7   <64   <64   <72   μVrms   INV					_			_
STATIC, DC PERFORMANCE* input offset voltage1<4.0								II .
* input offset voltage average temperature coefficient averag							r -	
average temperature coefficient input bias current non-inverting average temperature coefficient input bias current non-inverting average temperature coefficient inverting average temperature coefficient inverting input capacitance output impedance $\begin{pmatrix} 10 & <25 & <25 & \mu V \\ 5.0 & <29 & <21 & <31 & \mu A \\ 5.0 & <29 & <21 & <31 & \mu A \\ 5.0 & <29 & <21 & <31 & \mu A \\ 5.0 & <29 & <21 & <31 & \mu A \\ 5.0 & <125 & <125 & <125 & nA/°C & DIBN \\ 6.0 & <31 & <15 & <35 & \mu A & IBI \\ 125 & <200 & <200 & <200 & <200 & nA/°C & DIBI \\ 6.0 & >45 & >45 & >45 & >45 & dB & PSRR \\ 6.0 & >40 & >40 & >40 & >40 & dB & CMRR \\ 7.0 & & & & & & & & & & & & & & & & & & &$			1 1	<4.0	<2.0	<4.5	mV	VIO
* input bias current average temperature coefficient average			II I					II .
* input bias current average temperature coefficient average can be average temperature coefficient average can be average temperature coefficient average temperature coefficient average temperature coefficient average temperature coefficient average can be averag		non-inverting	5.0				˙μA	IBN
average temperature coefficient $125$ $<200$ $<200$ $<200$ $\text{nÅ/°C}$ DIBI * power supply rejection ratio $50$ $>45$ $>45$ $>45$ $>45$ $dB$ PSRR common mode rejection ratio $46$ $>40$ $>40$ $>40$ $dB$ CMRR * supply current no load $25$ $<27$ $<27$ $<29$ mA ICC **  **MISCELLANEOUS PERFORMANCE**  non-inverting input resistance por input resistance non-inverting input capacitance output impedance $200$		G	50	<125	<125	<125	nÀ/°C	II .
* power supply rejection ratio common mode rejection ratio $46$ $46$ $40$ $40$ $40$ $40$ $40$ $40$ $40$ $40$		inverting						II .
common mode rejection ratio $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				ll .			II .	
* supply current no load 25 <27 <29 mA ICC MISCELLANEOUS PERFORMANCE non-inverting input resistance non-inverting input capacitance output impedance $@$ 100MHz $=$ 25 <27 <29 mA ICC $=$ 400 $=$ 100 $=$ 200 $=$ 400 $=$ 8IN $=$ 6IN $=$ 7IN $=$ 7								
MISCELLANEOUS PERFORMANCE         non-inverting input resistance       DC       400       >100       >200       >400       RIN         non-inverting input capacitance output impedance $0$ 1.3       <2.5		no load						
non-inverting input resistance DC $400$ $>100$ $>200$ $>400$ k $\Omega$ RIN non-inverting input capacitance $1.3$ $<2.5$ $<2.5$ $<2.5$ pF CIN output impedance @ 100MHz $5,37$ $ \Omega, nH$ RO		110 1044	20	\		\20	1117 (	100
non-inverting input capacitance		DC:	400	>100	>200	>400	kO	RIN
output impedance @ 100MHz     5, 37   -   -   Ω, nH   RO	non-inverting input resistance							
		@ 100MHz		_	_	_		
		no load		>±11	>±11	>±11	1 1	VO

Min/max ratings are based on product characterization and simulation. Individual parameters are tested as noted. Outgoing quality levels are determined from tested parameters.

## Absolute Maximum Ratings

 $\rm V_{\rm CC}$ ±100mA I<sub>o</sub>  $|V_{CC}| > 15V \pm (30-|V_{CC}|)V$ common mode input voltage, Vo  $|V_{CC}| \le 15V \pm |V_{CC}|V$ differential input voltage thermal resistance (see thermal model) junction temperature +175°C operating temperature AI: -25°C to +85°C AK/AM/HXC/HXA: -55°C to +125°C -65°C to +150°C storage temperature lead temperature (soldering 10s) +300°C

## **Recommended Operating Conditions**

 $V_{CC}$ ±5V to ±15V ±75mA common mode input voltage  $\pm (|V_{CC}| -5)V$ gain range ±1 to ±5

AI/AK/AM/HXC/HXA 100% tested at +25°C note 1:

100% tested at +25°C and sample AK/AM/HXC/HXA + tested at -55°C and +125°C

sample tested at +25°C

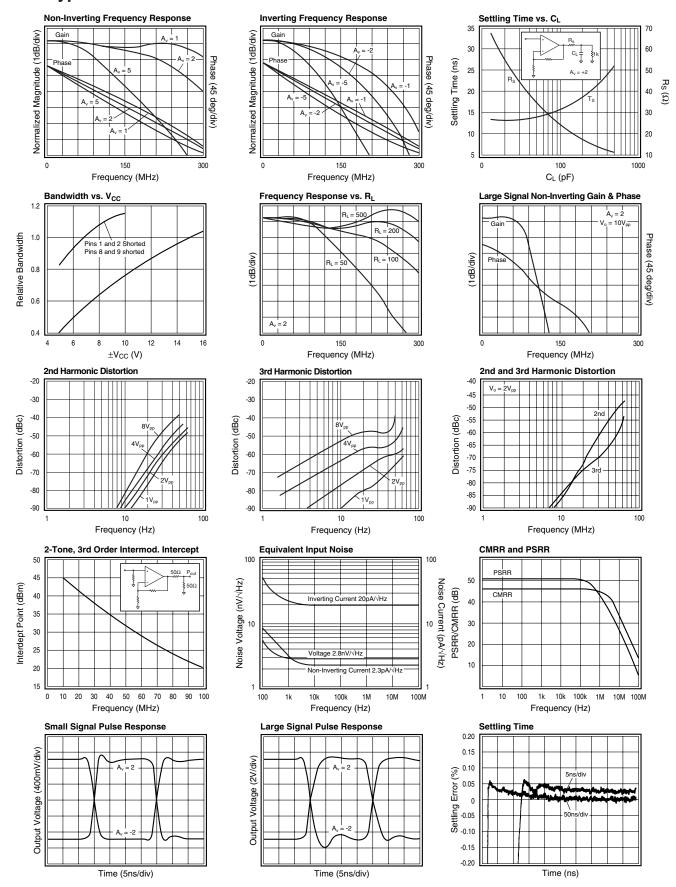
The output amplitude used in testing is  $0.63V_{pp}$ . Performance note 2:

is guaranteed for conditions listed.

† Al

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## KH232 Typical Performance Characteristics ( $T_A = +25^{\circ}\text{C}$ , $A_v = +2$ , $V_{CC} = \pm 15\text{V}$ , $R_L = 100\Omega$ , $R_f = 250\Omega$ ; unless specified)



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#### Operation

The KH232 is based on the current feedback op amp topology, a design that uses current feedback instead of the usual voltage feedback.

The use of the KH232 is basically the same as that of the conventional op amp (see Figures 1 and 2). Since the device is designed specifically for low gain applications, the best performance is obtained when the circuit is used at gains between  $\pm 1$  and  $\pm 5$ . Additionally, performance is optimum when a  $250\Omega$  feedback resistor is used.

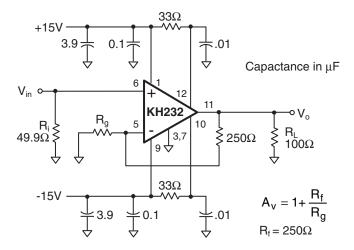


Figure 1: Recommended non-inverting gain circuit

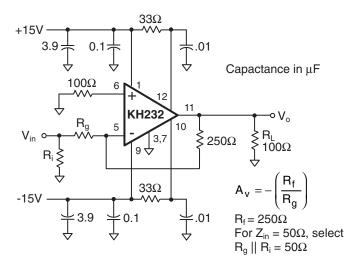


Figure 2: Recommended inverting gain circuit

#### **Layout Considerations**

To assure optimum performance the user should follow good layout practices which minimize the unwanted coupling of signals between nodes. During initial bread-boarding of the circuit use direct point to point wiring, keeping the lead lengths to less than 0.25". The use of solid, unbroken ground plane is helpful. Avoid wire-wrap type pc boards and methods. Sockets with small, short pin receptacles may be used with minimal performance degradation although their use is not recommended.

During pc board layout keep all traces short and direct The resistive body of R<sub>g</sub> should be as close as possible to pin 5 to minimize capacitance at that point. For the same reason, remove ground plane from the vicinity of pins 5 and 6. In other areas, use as much ground plane as possible on one side of the board. It is especially important to provide a ground return path for current from the load resistor to the power supply bypass capacitors. Ceramic capacitors of 0.01 to 0.1 µf (with short leads) should be less than 0.15 inches from pins 1 and 9. Larger tantalum capacitors should be placed within one inch of these pins. V<sub>CC</sub> connections to pins 10 and 12 can be made directly from pins 9 and 1, but better supply rejection and settling time are obtained if they are separately bypassed as in figures 1 and 2. To prevent signal distortion caused by reflections from impedance mismatches, use terminated microstrip or coaxial cable when the signal must traverse more than a few inches.

Since the pc board forms such an important part of the circuit, much time can be saved if prototype boards of any high frequency sections are built and tested early in the design phase. Evaluation boards designed for either inverting or non-inverting gains are available.

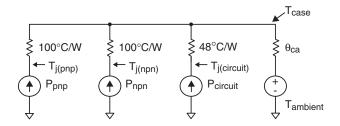
### Offset Voltage Adjustment

If trimming of the input offset voltage ( $V_{os} = V_{ni} - V_{in}$ ) is desired, a resistor value of  $10k\Omega$  to  $1M\Omega$  placed between pins 8 and 9 will cause  $V_{os}$  to become more negative by 8mV to 0.2mV respectively. Similarly, a resistor placed between pins 1 and 2 will cause  $V_{os}$ , to become more positive.

#### **Thermal Considerations**

At high ambient temperatures or large internal power dissipations, heat sinking is required to maintain acceptable junction temperatures. Use the thermal model on the previous page to determine junction temperatures. Many styles of heat sinks are available for TO-8 packages; the Thermalloy 2240 and 2268 are good examples. Some heat sinks are the radial fin type which cover the pc board and may interfere with external components. An excellent solution to this problem is to use surface mounted resistors and capacitors. They have a very low profile and actually improve high frequency performance. For use of these heat sinks with conventional components, a 0.1" high spacer can be inserted under the TO-8 package to allow sufficient clearance.

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$$P_{(circuit)} = (I_{CC})((+V_{CC}) - (V_{CC}))$$
 where  $I_{CC} = 14mA$  at ±15V

$$P_{(xxx)} = [(\pm V_{CC}) - V_{out} - (I_{col}) (R_{col} + 4)] (I_{col}) (\%Duty)$$

For positive  $V_o$  and  $V_{CC}$ , this is the power in the npn device. For negative  $V_o$  and  $V_{CC}$ , this is the power in the pnp device.

 $I_{col} = V_o/R_L$  or 12mA, whichever is greater. (Include feedback R in  $R_I$ .)

 $R_{col}$  is a resistor (33 $\!\Omega$  recommended) between the xxx collector and  $\pm V_{CC}.$ 

The limiting factor for output current and voltage is junction temperature. Of secondary importance is  $I_{(out)}$ , which should not exceed 150mA.

$$\begin{split} T_{j(pnp)} &= P_{(pnp)} \ (100 + \theta_{ca}) + (P_{(cir)} + P_{(npn)})(\theta_{ca}) + T_a, \\ similar \ for \ T_{i(npn)}. \end{split}$$

$$T_{i(cir)} = P_{(cir)}(48 + \theta_{ca}) + (P_{(pnp)} + P_{(npn)})(\theta_{ca}) + T_a.$$

 $\theta_{\text{ca}}$  = 65°C/W for the KH232 without heat sink in still air. 35°C/W for the KH232 with a Thermalloy 2268A heat sink in still air.

15°C/W for the KH232 with a Thermalloy 2268A heat sink at 300 ft/min air.

(Thermalloy 2240A works equally as well.)

For example, with the KH232 operating at  $\pm 15V$  while driving a  $100\Omega$  load at  $15V_{pp}$  output (50% duty cycle pulse waveform, DC = 0),  $P_{(npn)} = P_{(pnp)} = 190$ mW ( $R_{col} = 33$ ) and  $P_{(cir)} = 0.42$ W. Then with the Thermalloy 2268 heat sink and air flow of 300 ft/min the output transistors'  $T_j$  is 31°C above ambient and worst case  $T_j$  in the rest of the circuit is 32°C above ambient. In still air, however, the rise in  $T_j$  is 47°C and 48°C, respectively. With no heat sink, the rise in  $T_j$  is 71°C and 72°C, respectively! Under most conditions, **HEAT SINKING IS REQUIRED**.

Other methods of heat sinking may be used, but for best results, make contact with the base of the KH232 package, use a large thermal capacity heat sink and use forced air convection.

## Low V<sub>CC</sub> Operation: Supply Current Adjustment

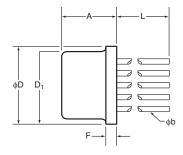
The KH232 is designed to operate on supplies as low as  $\pm 5V$ . In order to improve full bandwidth at reduced supply voltages, the supply current (I<sub>CC</sub>) must be increased. The plot of Bandwidth vs. V<sub>CC</sub>, shows the effect of shorting pins 1 and 2 and pins 8 and 9; this will increase both bandwidth and supply current. Care should be taken to not exceed the maximum junction temperatures; for this reason this technique should not be used with supplies exceeding  $\pm 10V$ . For intermediate values of V<sub>CC</sub>, external resistors between pins 1 and 2 and pins 8 and 9 can be used.

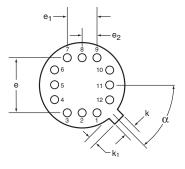
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## **KH232 Package Dimensions**





TO-8						
SYMBOL	INC	HES	MILIMETERS			
STIMBOL	Minimun	Maximum	Minimum	Maximum		
А	0.142	0.181	3.61	4.60		
фЬ	0.016	0.019	0.41	0.48		
φD	0.595	0.605	15.11	15.37		
φD <sub>1</sub>	0.543	0.555	13.79	14.10		
е	0.400	) BSC	10.16 BSC			
e <sub>1</sub>	0.200 BSC		5.08 BSC			
e <sub>2</sub>	0.100 BSC		2.54 BSC			
F	0.016	0.030	0.41	0.76		
k	0.026	0.036	0.66	0.91		
k <sub>1</sub>	0.026	0.036	0.66	0.91		
L	0.310	0.340	7.87	8.64		
α	45° BSC		45° BSC			

#### NOTES:

Seal: cap weld Lead finish: gold per MIL-M-38510 Package composition: Package: metal

Lid: Type A per MIL-M-38510

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